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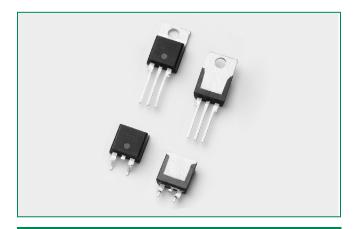






# S8016xA Series

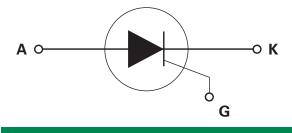




#### **Main Features**

Symbol	Value	Unit
I <sub>T(RMS)</sub>	16	А
V <sub>DRM</sub> /V <sub>RRM</sub>	800	V
l <sub>GT</sub>	50	mA

# **Schematic Symbol**



#### **Description**

The Littelfuse SCR S8016xA series are specifically designed for Electric Vehicle On-Board Charger (EVOBC) applications. This SCR AC line input rectifier can handle Level 1 charging up to 16Arms at 120V, and Level 2 charging up to 16A rms at 240V at 100°C and up to 25A rms for 80°C. Its excellent AC handling capability and surge robustness makes this series an ideal switch for these input rectifiers.

#### **Features & Benefits**

- $\bullet$  V  $_{\rm DRM}$  800V, I  $_{\rm T}$  25rms to handle input from 100-250V line AC
- High di/dt of 375/µsec enables handling of 3kA 8/20 surge current operationally
- High V<sub>DSM</sub>/V<sub>RSM</sub> of 1300V, high dv/dt of 2000V/ µsec prevents SCR mistriggering during 6kV 1.2/50-8/20 surge event with minimal over voltage protection or snubber circuit
- Available in the compact TO-263 SMT package
- AEC-Q101 Fully Compliant
- Halogen free and RoHS compliant

#### **Applications**

Input rectification of AC line input for EVOBC applications.

### **Absolute Maximum Ratings**

Symbol	Parameter	Test Conditions	Value	Unit	
V <sub>DSM</sub> /V <sub>RSM</sub>	Peak non-repetitive blocking voltage	Pw=100µs	1300	V	
	RMS on-state current	T <sub>c</sub> =100°C	16	А	
T(RMS)	Tilvio on-state current	T <sub>c</sub> =80°C	25	A	
	Average on-state current	T <sub>c</sub> =100°C	10	A	
I <sub>T(AV)</sub>	Average on-state current	T <sub>c</sub> =80°C	16		
1	Pook pop ropotitivo curao current	single half cycle; f=50Hz; T <sub>J</sub> (initial)=25°C	188	A	
I <sub>TSM</sub>	Peak non-repetitive surge current	single half cycle; f=60Hz; T <sub>J</sub> (initial)=25°C	225	А	
l²t	I²t Value for fusing	t <sub>p</sub> =8.3 ms	210	A <sup>2</sup> s	
I <sub>PP</sub>	Non-repetitive peak surge current	with Littelfuse MOV V20E420AUTO across line; $T_J$ =125°C, 11.2/50-8/20 combination wave, $I_T$ =1A	2400	А	
di/dt	Critical rate of rise of on-state current	T <sub>J</sub> =125°C	375	A/µs	
I <sub>GM</sub>	Peak gate current	T <sub>J</sub> =125°C	3.0	А	
P <sub>G(AV)</sub>	Average gate power dissipation	T <sub>J</sub> =125°C	0.6	W	
T <sub>stg</sub>	Storage temperature range		-40 to 150	°C	
T <sub>J</sub>	Operating junction temperature range		-40 to 125	°C	

# Electrical Characteristics (T<sub>J</sub> = 25°C, unless otherwise specified)

Symbol	Test Conditions	Value	Unit	
		MIN.	15	mA
I <sub>GT</sub>	$V_D = 12V$ ; $R_L = 30\Omega$	MAX.	50	IIIA
V <sub>GT</sub>		MAX.	1.5	V
	$V_D = V_{DRM}$ ; gate open; $T_J = 125$ °C	MIN.	2000	V/µs
dv/dt	1.2/50 pulse wave, with 250V AC with Littelfuse MOV V20E420AUTO across	MIN.	5	KV/μs
V <sub>GD</sub>	$V_D = V_{DRM}$ ; $R_L = 3.3 \text{ k}\Omega$ ; $T_J = 125$ °C	MIN.	0.2	V
I <sub>H</sub>	I <sub>T</sub> =400mA (initial)	MAX.	150	mA
t <sub>q</sub>	$I_T$ =0.5A; $t_p$ =50µs; dv/dt=5V/µs; di/dt=-30A/µs	MAX.	35	μs
t <sub>gt</sub>	$I_{g}=2 \times I_{gT}$ ; PW=15 $\mu$ s; $I_{T}$ =40A	TYP.	2	μs

#### **Static Characteristics**

Symbol	Test Conditions			Value	Unit
V <sub>TM</sub>		$I_{T}=32A; t_{p}=380 \mu s$ MAX.		1.4	V
		T <sub>J</sub> =25°C		20	
I <sub>DRM</sub> / I <sub>RRM</sub>	@ V <sub>DRM</sub> / V <sub>RRM</sub>	T <sub>J</sub> =100°C	MAX.	1000	μΑ
		T <sub>J</sub> =125°C		2000	

#### **Thermal Resistances**

Symbol	Parameter	Value	Unit
R <sub>e(J-C)</sub>	Junction to case (AC)	1.0	°C/W

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature

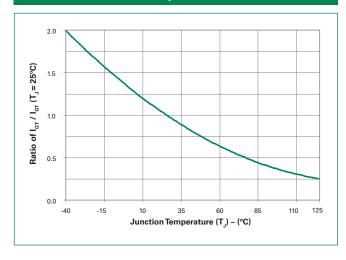


Figure 2: Normalized DC Gate Trigger Voltage vs. Junction Temperature

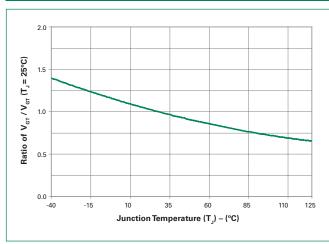




Figure 3: Normalized DC Holding Current vs. Junction Temperature

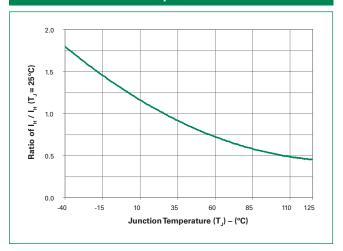


Figure 5: Power Dissipation (Typical) vs. RMS On-State Current

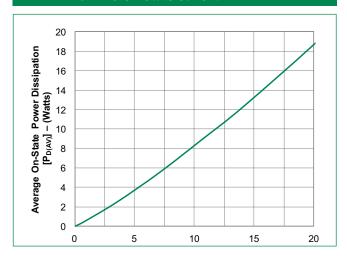


Figure 7: Maximum Allowable Case Temperature vs. Average On-State Current

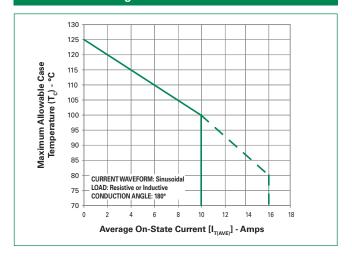


Figure 4: On-State Current vs. On-State Voltage (Typical)

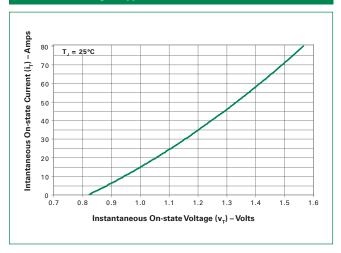
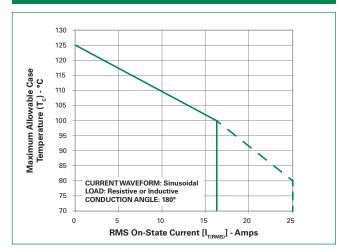
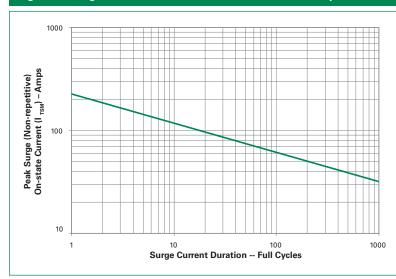


Figure 6: Maximum Allowable Case Temperature vs. RMS On-State Current



# Figure 8: Surge Peak On-State Current vs. Number of Cycles



SUPPLY FREQUENCY: 60 Hz Sinusoidal LOAD: Resistive

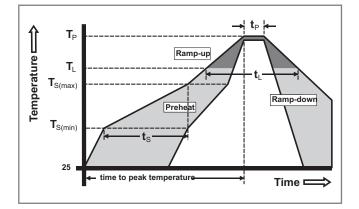
RMS On-State Current: [ $I_{T(RMS)}$ ]: Maximum Rated Value at Specified Case Temperature

#### Notes:

- 1. Gate control may be lost during and immediately following surge current interval.
- Overload may not be repeated until junction temperature has returned to steady-state rated value.

# **Soldering Parameters**

Reflow Co	ndition	Pb – Free assembly
	-Temperature Min (T <sub>s(min)</sub> )	150°C
Pre Heat	-Temperature Max (T <sub>s(max)</sub> )	200°C
	-Time (min to max) (t <sub>s</sub> )	60 – 180 secs
Average ra	amp up rate (LiquidusTemp) k	5°C/second max
$T_{S(max)}$ to $T_{L}$	- Ramp-up Rate	5°C/second max
Reflow	-Temperature (T <sub>L</sub> ) (Liquidus)	217°C
nellow	-Time (t <sub>L</sub> )	60 – 150 seconds
PeakTemp	erature (T <sub>P</sub> )	260 <sup>+0/-5</sup> °C
Time with Temperatu	in 5°C of actual peak ure (t <sub>p</sub> )	20 – 40 seconds
Ramp-dov	vn Rate	5°C/second max
Time 25°C	to peakTemperature (T <sub>P</sub> )	8 minutes Max.
Do not exc	ceed	280°C



#### **Physical Specifications**

Terminal Finish	100% Matte Tin-plated
Body Material	UL Recognized epoxy meeting flammability rating V-0
Lead Material	Copper Alloy

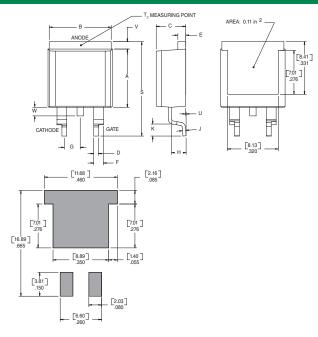
#### **Design Considerations**

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

### **Environmental Specifications**

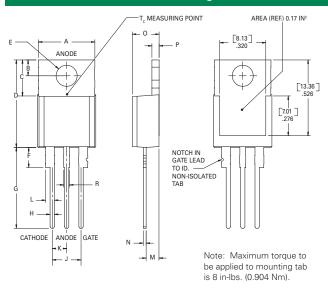
Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	JESD22 A-104 Appendix 6 -55°C to 150°C, 15-minute dwell, 1000 cycles
Autoclave (Pressure Cooker Test)	EIA/JEDEC: JESD22-A102 121°C, 100%RH, 15psig, 96hours
Biased Temperature & Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
Intermittent Operational Life	T <sub>A</sub> =25°C, ΔTJ ≥ 100°C, 1008hrs
Resistance to Solder Heat	JESD22 A-111: 260°C, 10 seconds
Solderability	ANSI/J-STD-002, category 3, Test A

# Dimensions –TO- 263AB (N-package) — D²-Pak Surface Mount



Dimension	Inc	hes	Millin	neters
Dimension	Min	Max	Min	Max
А	0.360	0.370	9.14	9.40
В	0.380	0.420	9.65	10.67
С	0.178	0.188	4.52	4.78
D	0.025	0.035	0.64	0.89
Е	0.045	0.060	1.14	1.52
F	0.060	0.075	1.52	1.91
G	0.095	0.105	2.41	2.67
Н	0.092	0.102	2.34	2.59
J	0.018	0.024	0.46	0.61
K	0.090	0.110	2.29	2.79
S	0.590	0.625	14.99	15.88
V	0.035	0.045	0.89	1.14
U	0.002	0.010	0.05	0.25
W	0.040	0.070	1.016	1.78

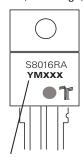
# Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Incl	nes	Millin	neters
Difficusion	Min	Max	Min	Max
А	0.380	0.420	9.65	10.67
В	0.105	0.115	2.67	2.92
С	0.230	0.250	5.84	6.35
D	0.590	0.620	14.99	15.75
Е	0.142	0.147	3.61	3.73
F	0.110	0.130	2.79	3.30
G	0.540	0.575	13.72	14.61
Н	0.025	0.035	0.64	0.89
J	0.195	0.205	4.95	5.21
K	0.095	0.105	2.41	2.67
L	0.060	0.075	1.52	1.91
М	0.085	0.095	2.16	2.41
N	0.018	0.024	0.46	0.61
0	0.178	0.188	4.52	4.78
Р	0.045	0.060	1.14	1.52
R	0.038	0.048	0.97	1.22

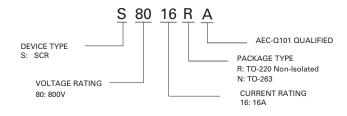
# **Part Marking System**

TO-220 AB - (R Package) TO-263 (N Package)



Date Code Marking Y:Year Code M: Month Code XXX: Lot Trace Code

# **Part Numbering System**



### **Packing Options**

Part Number	Marking	Weight	Packing Mode	Base Quantity	Package
S8016RATP	S8016RA	1.6g	Tube	500 (50 per tube)	TO-220R
S8016NARP	S8016NA	1.6g	Embossed Carrier	500	TO-263





# TO-263 Embossed Carrier Reel Pack (RP) Specifications

#### Meets all EIA-481-2 Standards

